

ABSTRACT

Provided are: a semiconductor treatment liquid comprising high-purity isopropyl alcohol, wherein the concentration of the oxolane compound expressed in formula (1) below when held for 60 days in a nitrogen atmosphere at 50°C in a SUS304 container is 25 ppb or less on a mass basis in relation to the isopropyl alcohol; and a method for manufacturing said semiconductor treatment liquid. In the formula, R¹ and R² each independently represent a hydrogen atom or a C1-3 alkyl group, and the total number of carbon atoms in R¹ and R² is 3 or less. R³ represents a hydrogen atom or an isopropyl group.